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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/053,963	01/22/2002	Aron T. Lunde	MICS:0214	5214	
	7590 08/06/200 ODER (MICRON TEC	EXAMINER			
P.O. BOX 692289			NGUYEN, KHIEM D		
HOUSTON, T	X 77269-2289		ART UNIT PAPER NUMBER		
			2823		
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			MAIL DATE	DELIVERY MODE	
•		•	08/06/2007	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

		Application No		Annlinent(-)			
Office Action Summary		Application No	<b>'·</b>	Applicant(s)			
		10/053,963	·	LUNDE, ARON T.			
		Examiner		Art Unit			
· · · · · · · · · · · · · · · · · · ·		Khiem D. Nguy		2823			
Period fo	The MAILING DATE of this communication app or Reply	ears on the cov	er sheet with the co	rrespondence address			
WHIC - Exter after - If NO - Failu Any	ORTENED STATUTORY PERIOD FOR REPLY CHEVER IS LONGER, FROM THE MAILING DANSIONS of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. operiod for reply is specified above, the maximum statutory period were to reply within the set or extended period for reply will, by statute, reply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS C 36(a). In no event, how will apply and will expire, cause the application	OMMUNICATION wever, may a reply be time e SIX (6) MONTHS from to to become ABANDONED	ely filed he mailing date of this communication (35 U.S.C. § 133).			
Status							
1)⊠	Responsive to communication(s) filed on <u>07 M</u> .	ay 2007.		•			
_	<u> </u>						
3)	Since this application is in condition for allowance except for formal matters, prosecution as to the ments is						
	closed in accordance with the practice under E	x parte Quayle,	1935 C.D. 11, 45	3 O.G. 213.			
Dispositi	ion of Claims						
5)⊠ 6)⊠	Claim(s) <u>1-28</u> is/are pending in the application. 4a) Of the above claim(s) is/are withdray Claim(s) <u>28</u> is/are allowed. Claim(s) <u>1,2,5,8-10,13-15,18,19,21-23,26 and</u> Claim(s) <u>3,4,6,7,11,12,16,17,20,24 and 25</u> is/a Claim(s) are subject to restriction and/or	wn from conside 27 is/are rejected to.	ed.	9			
Applicati	ion Papers						
10)⊠	The specification is objected to by the Examine The drawing(s) filed on 22 January 2002 is/are: Applicant may not request that any objection to the Replacement drawing sheet(s) including the correction of the oath or declaration is objected to by the Example.	: a)⊠ accepted drawing(s) be hel ion is required if t	d in abeyance. See he drawing(s) is obje	37 CFR 1.85(a). ected to. See 37 CFR 1.121(d	i).		
Priority ι	ınder 35 U.S.C. § 119						
12)□ a)l	Acknowledgment is made of a claim for foreign  All b) Some * c) None of:  1. Certified copies of the priority documents  2. Certified copies of the priority documents  3. Copies of the certified copies of the priorical application from the International Bureau  See the attached detailed Office action for a list	s have been red s have been red nty documents h u (PCT Rule 17.	ceived. ceived in Application nave been receive 2(a)).	on No d in this National Stage			
2)  Notic 3) Infor	e of References Cited (PTO-892) se of References Cited (PTO-892) se of Draftsperson's Patent Drawing Review (PTO-948) mation Disclosure Statement(s) (PTO/SB/08) sr No(s)/Mail Date	4) [_ 5) [_ 6) [_	Interview Summary ( Paper No(s)/Mail Da Notice of Informal Pa Other:	e			

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### **DETAILED ACTION**

### New Grounds of Rejection

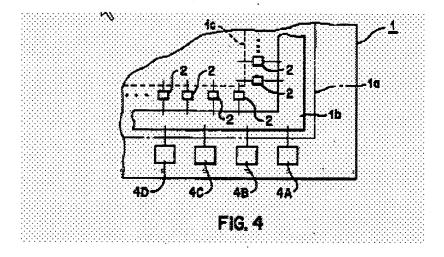
### Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 2. Claims 1, 2, 5, 8-10, 13-15, 18, 19, 21-23, 26 and 27 are rejected under 35 U.S.C. 102(b) as being anticipated by Shibata (U.S. Patent 5,661,407).

In re claim 1, **Shibata** discloses a method for forming a die, the method comprising, forming a die 1 on a wafer, the die 1 having one or more lateral edges, an active portion 1c comprising integrated circuitry, and an inactive portion formed between the active portion and at least one lateral edge of the one or more lateral edges of the die 1, wherein the die 1 has a plurality of input bond pads 2 formed on the active portion 1c (col. 6, lines 14-20 and FIG. 4);



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forming at least one test pad 4A-D (col. 6, line 29) on the die 1; and forming a conductive path (wire bonding) (col. 6, lines 27-28) between the at least one input bond pad 2 and the at least one test pad 4A-D, wherein a portion of the conductive path is formed on the inactive portion of the die between the at least one lateral edge of the die 1 and the active portion 1c of the die 1 (col. 6, lines 26-35 and FIG. 4).

In re claim 2, as applied to claim 1 above, <u>Shibata</u> discloses all claimed limitations including the limitation wherein the plurality of test pads 4A-D is formed on the active portion 1c of the die 1 (col. 6, lines 13-21).

In re claim 5, as applied to claim 1 above, <u>Shibata</u> discloses all claimed limitations including the limitation wherein severing the conductive path at a point outside of the active portion of the die 1 (col. 6, lines 32-34).

In re claim 8, as applied to claim 1 above, **Shibata** discloses all claimed limitations including the limitation wherein at least one test pad 4A-D is of a sufficient size so as to be accessible by a testing apparatus (col. 4, lines 45-51).

In re claim 9, Shibata discloses a die assembly formed on a wafer, the die assembly comprising, a die 1 formed on a wafer, the die 1 having one or more lateral edges, an active portion 1c comprising integrated circuitry, and an inactive portion formed between the active portion 1c and at least one lateral edge of the one or more lateral edges of the die 1; at least one input bond pad 2 formed on the active portion of the die 1 (col. 6, lines 14-20 and FIG. 4);

at least one test pad 4A-D (col. 6, line 29) formed entirely on the die 1; and a conductive path (wire bonding) (col. 6, lines 27-28) that electrically couples the at least

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one input bond pad 2 to the at least one test pad 4A-D, wherein a portion of the conductive path is formed on the inactive portion between the at least one lateral edge of the die 1 and the active portion of the die 1 (col. 6, lines 26-35 and FIG. 4).

In re claim 10, as applied to claim 9 above, <u>Shibata</u> discloses all claimed limitations including the limitation wherein the plurality of test pads 4A-D is formed on the active portion 1c of the die 1 (col. 6, lines 13-21).

In re claim 13, as applied to claim 9 above, <u>Shibata</u> discloses all claimed limitations including the limitation wherein at least one test pad 4A-D is of a sufficient size so as to be accessible by a testing apparatus (col. 4, lines 45-51).

In re claim 14, Shibata discloses a method for preparing a die on a wafer for testing by a testing apparatus, the method comprising, forming a die 1 on a wafer, the die 1 having one or more lateral edges, an active portion 1c comprising integrated circuitry, and an inactive portion formed between the active portion 1c and at least one lateral edge of the one or more lateral edges of the die 1; forming a plurality of input bond pads 2 on the active portion 1c (col. 6, lines 14-20 and FIG. 4);

forming a plurality of test pads 4A-D (col. 6, line 29) entirely on the die 1, wherein the plurality of test pads 4A-D accessible to the testing apparatus (col. 4, lines 45-51), at least one of the plurality of test pads 4A-D corresponding to at least one of the plurality of input bond pads 2; forming a conductive path (wire bonding) (col. 6, lines 27-28) between the at least one of the plurality of test pads 4A-D and the at least one of the plurality of input bond pads 2, wherein a portion of the conductive path is formed on the active portion between the at least one lateral edge of the die and the active portion 1c of

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the die 1 (col. 6, lines 26-35 and FIG. 4); and testing the die 1 by contacting the at least one of plurality of test pads 4A-D with the testing apparatus (col. 8, lines 58-65).

In re claim 15, as applied to claim 14 above, **Shibata** discloses all claimed limitations including the limitation wherein the plurality of test pads 4A-D is formed on the active portion 1c of the die 1 (col. 6, lines 13-21).

In re claim 18, as applied to claim 14 above, <u>Shibata</u> discloses all claimed limitations including the limitation wherein severing the conductive path at a point outside of the active portion 1c of the die 1 (col. 6, lines 32-34).

In re claim 19, as applied to claim 16 above, **Shibata** discloses all claimed limitations including the limitation wherein severing the conductive path at a point within the inactive portion (FIG. 4).

In re claim 21, as applied to claim 14 above, <u>Shibata</u> discloses all claimed limitations including the limitation wherein at least one of the plurality of test pad 4A-D is larger in size than the at least one of the plurality of the input bond pads 2 (col. 6, lines 16-17 and FIG. 4).

In re claim 22, <u>Shibata</u> discloses a die comprising: one or more lateral edges, an active portion 1c comprising integrated circuitry; an inactive portion formed between the active portion 1c and at least one lateral edge of the one or more lateral edges of the die 1, a plurality of input bond pads 2 formed on the active portion 1c (col. 6, lines 14-20 and FIG. 4);

a plurality of test pads 4A-D (col. 6, line 29) formed entirely on the die 1, and the plurality of conductive lines (wire bonding) (col. 6, lines 27-28), wherein each of the

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conductive lines is initially formed to electrically couple at least one of the plurality of input bond pads 2 to at least one of the plurality of test pads 4A-D, and wherein a portion of each of the conductive lines is formed on the inactive portion between the at least one

lateral edge of the die 1 and the active portion 1c of the die 1 (col. 6, lines 26-35 and FIG.

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4).

In re claim 23, as applied to claim 22 above, <u>Shibata</u> discloses all claimed limitations including the limitation wherein the plurality of test pads 4A-D is formed on the active portion 1c of the die 1 (col. 6, lines 13-21).

In re claim 26, as applied to claim 25 above, **Shibata** discloses all claimed limitations including the limitation wherein the portion of each of the conductive lines is configured to be severed when the die 1 is separated from the wafer (col. 6, lines 32-34).

In re claim 27, as applied to claim 22 above, Shibata discloses all claimed limitations including the limitation wherein the at least one of the plurality of test pads 4A-D is larger in size than the at least one of the plurality of input bond pads 1 (col. 6, lines 16-17).

#### Allowable Subject Matter

- 3. Claim 28 is allowed over prior art of record
- 4. Claims 3, 4, 6, 7, 11, 12, 16, 17, 20, 24 and 25 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

#### Reasons For Allowance

5. The following is an examiner's statement of reasons for allowance:

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After further search and consideration of Applicant's response filed on May 07<sup>th</sup>, 2007 (see Applicant's response in Page 11 of the May 07<sup>th</sup>, response), it is determined that the prior art of record neither anticipates nor renders obvious the claimed subject matter of the instant application as a whole taken alone or in combination, in particular, prior art of record does not teach "wherein a portion of said each of said conductive lines is formed on a scribe area outside the die", as recited in the independent claim 28.

## Response to Applicant's Amendment and Arguments

6. Applicants' arguments with respect to claims 1-28 have been considered but are moot in view of the new ground(s) of rejection necessitated by the amendment filed on May 07<sup>th</sup>, 2007.

#### Conclusion

7. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, THIS ACTION IS MADE FINAL. See MPEP § 706.07(a).

Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a). A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

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Correspondence

8. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Khiem D. Nguyen whose telephone number is (571) 272-

1865. The examiner can normally be reached on Monday-Friday (8:30 AM - 5:30 PM).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Matthew S. Smith can be reached on (571) 272-1907. The fax phone number

for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the

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Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO

Customer Service Representative or access to the automated information system, call

800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/KN/

July 30, 2007

BROOK KEBEDE

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